

ABSTRACT OF THE DISCLOSURE

The invention provides a connection substrate, a method of manufacturing a connection substrate, a semiconductor device, a method of manufacturing a semiconductor device which can narrow a width and a pitch of wiring, enables a multi-layer wiring, and reduces an effect of radiation heat, such as a heating tool when a semiconductor chip is mounted so that a damage such as wire disconnection or the like due to an external force is not generated. First metal wires are formed on a surface of a first glass base. An insulating film is formed on the first metal wires, and second metal wires are formed on the insulating film. Thus, in a connection substrate, the first glass base has no flexibility, so deformation is not generated. Because of this, during interim processes wherein metal wires are formed, such as in an exposure process, a glass base does not move in a depth of field direction. Therefore, exposure with a narrow width can be performed, so metal wires having a narrow pitch and a narrow width can be formed.

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